

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device comprises: a first light-emitting element having a first laser part, an insulating layer, and an ohmic electrode layer; and a second light-emitting element having a second laser part, an insulating layer, and an ohmic electrode layer. The first laser part has a ridge waveguide, and is formed by stacking thin films of group-III nitride compound semiconductors (for example, GaN-based semiconductors). The second laser part has a ridge waveguide, and is formed by stacking thin films of group III-V compound semiconductors (such as GaAs). The first laser part and the second laser part are integrally bonded to each other by the interposition of an adhesive metal layer which is formed between the ohmic electrode layers. This provides the semiconductor laser device with a small distance between the light-emitting spots of the laser parts.